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 TI Deposition of Ta₂O₅ and (TiO₂)-(Ta₂O₅) films from Ta(OEt)₄(DMAE) and Ti(OEt)₂(DMAE)₂, by IMOCVD
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 SO Journal de Physique IV: Proceedings (1999), 9(Pr8, Proceedings of the Twelfth European Conference on Chemical Vapour Deposition, 1999, Vol. 2), 569-573
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 PB EDP Sciences
 DT Journal
 LA English
 CC 75-1 (Crystallography and Liquid Crystals)
 AB Ta₂O₅ and (TiO₂)-(Ta₂O₅) films were deposited on Si at low temp. by injection metalorg. CVD (IMOCVD) using tetraethoxy(dimethylaminoethoxy)tantalum, Ta(OEt)₄(DMAE) and diethoxybis(dimethylaminoethoxy)titanium, Ti(OEt)₂(DMAE)₂ as precursors. O was used in some cases as oxidizing agent; nevertheless, films were also obtained without O. The influence of deposition conditions on the deposition process and structural properties of the films was studied by FTIR, electron-probe microanal. and XRD.
 IT 172901-22-3
 RL: PEP (Physical, engineering or chemical process); PROC (Process) (injection metalorg. of Ta₂O₅ films using precursor)
 RN 172901-22-3 HCAPLUS
 CN Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, (OC-6-23)- (9CI) (CA INDEX NAME)

